

| | | |
|-------|---------|---------|
| VDS | RDS(on) | ID@25°C |
| 1200V | 80mΩ | 36A |

Applications:

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- EV Charging
- Motor Drives

Features:

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness

Benefits:

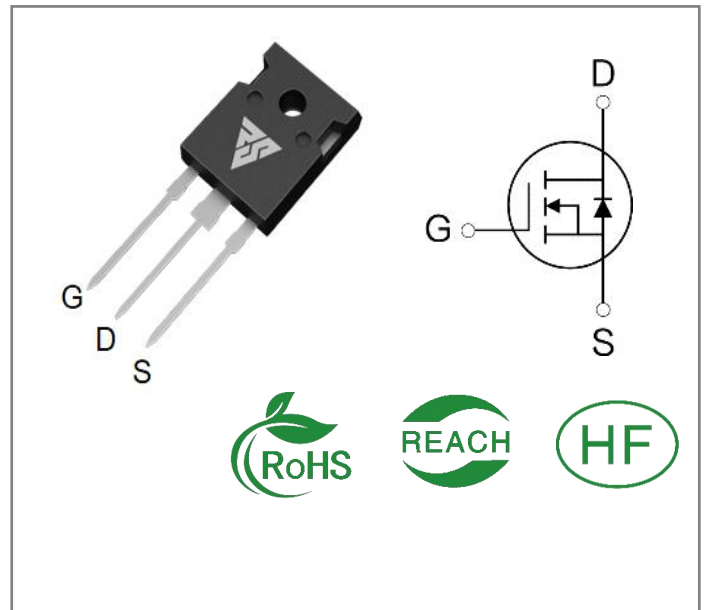
- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

Ordering Information

| Part Number | Package | Marking | Packing | Qty. |
|-------------|----------|------------|---------|--------|
| RSM120080W | TO-247-3 | RSM120080W | Tube | 30 PCS |

Maximum Ratings (TJ= 25°C unless otherwise specified)

| Symbol | Parameter | Value | Unit | Test Conditions | Note |
|-----------|--------------------------------------------|-----------------|------|-----------------------------------------|------|
| VDSmax | Drain - Source Voltage | 1200 | V | VGS=0V, ID =100μA | |
| VGSmax | Gate - Source Voltage | -10/+2 5 | V | Absolute maximum values | |
| VGSop | Gate - Source Voltage | -5/+20 | V | Recommended operational values | |
| ID | Continuous Drain Current | 36 24 | A | VGS=18V, TC =25°C VGS=18V, TC =100°C | |
| ID(pulse) | Pulsed Drain Current | 80 | A | Pulse width tp limited by TJmax | |
| PD | Power Dissipation | 192 | W | TC =25°C, TJ =150°C | |
| TL | Solder Temperature | 260 | °C | | |
| TJ, Tstg | Operating Junction and Storage Temperature | -40 to + 150 | °C | | |



Electrical Characteristics (T_J= 25°C unless otherwise specified)

| Symbol | Parameter | Min. | Typ. | Max. | Unit | Test Conditions | Note |
|---------------------|----------------------------------|------|------|------|------|--------------------------------------------------------------------------------------------------------------------------|------|
| V(BR)DSS | Drain-Source Breakdown Voltage | 1200 | | | V | V _{GS} =0V, I _D =100μA | |
| V _{GS(th)} | Gate Threshold Voltage | 2.0 | 2.4 | 4.0 | V | V _{GS} = V _D S, I _D S=5mA, TC =25°C | |
| | | | 1.8 | | V | V _{GS} = V _D S, I _D S=5mA, TC =150°C | |
| I _{DSS} | Zero Gate Voltage Drain Current | | 1 | 100 | μA | V _D S= 1200V, V _{GS} =0V | |
| I _{GSS} | Gate-Source Leakage Current | | 10 | 250 | nA | V _{GS} =25V, V _D S= 0V | |
| R _{DS(on)} | Drain-Source on-state Resistance | | 80 | 98 | mΩ | V _{GS} =20V, I _D =20A, TC =25°C | |
| | | | 140 | | | V _{GS} =20V, I _D =20A, TC =150°C | |
| C _{iss} | Input Capacitance | | 1475 | | pF | V _{GS} =0V, V _D S=1000 V, f=1MHz, V _{AC} =25 mV | |
| C _{oss} | Output Capacitance | | 94 | | | | |
| C _{rss} | Reverse Transfer Capacitance | | 11 | | | | |
| E _{ON} | Turn-On Switching Energy | | 564 | | μJ | V _D S =800V, V _{GS} =-5/20V, I _D = 20A, R _{G(ext)} = 2.5Ω, L= 200μH | |
| E _{OFF} | Turn-Off Energy | | 260 | | | | |
| t _{d(on)} | Turn-On Delay Time | | 9.3 | | ns | V _D S =800V, V _{GS} =-5/20 V, I _D = 20A, R _{G(ext)} =2.5 Ω , R _L =40Ω | |
| t _r | Rise Time | | 9.5 | | | | |
| t _{d(off)} | Turn-Off Delay Time | | 18 | | | | |
| t _f | Fall Time | | 7.6 | | | | |
| R _{G(int)} | Internal Gate Resistance | | 3.1 | | Ω | f=1 MHz, V _{AC} =25mV | |
| Q _{gs} | Gate to Source Charge | | 24 | | nC | V _D S=800V, V _{GS} =-5/20V, I _D =20A | |
| Q _{gd} | Gate to Drain Charge | | 15 | | | | |
| Q _g | Total Gate Charge | | 79 | | | | |

Reverse Diode Characteristics (T_J= 25°C unless otherwise specified)

| Symbol | Parameter | Typ. | Max | Unit | Test Conditions | Note |
|--------|----------------------------------|------|-----|------|--------------------------------------------|------|
| VSD | Diode Forward Voltage | 3.6 | | V | VGS=-5V, ISD = 10 A, T _J = 25°C | |
| | | 3.3 | | V | VGS=-5V, ISD= 10 A, T _J = 150°C | |
| IS | Continuous Diode Forward Current | | 44 | A | VGS=-5V, TC= 25°C | |
| trr | Reverse Recovery time | 35 | | ns | ISD= 20 A, VR = 800V | |
| Qrr | Reverse Recovery Charge | 91 | | nC | | |
| Irrm | Peak Reverse Recovery Current | 4.5 | | A | | |

Thermal Characteristics (T_J= 25°C unless otherwise specified)

| Symbol | Parameter | Typ. | Unit | Test Conditions | Note |
|------------------|---------------------------------------------|------|------|-----------------|------|
| R _{θJC} | Thermal Resistance from Junction to Case | 0.6 | °C/W | | |
| R _{θJA} | Thermal Resistance From Junction to Ambient | 40 | | | |

Typical Feature Curve

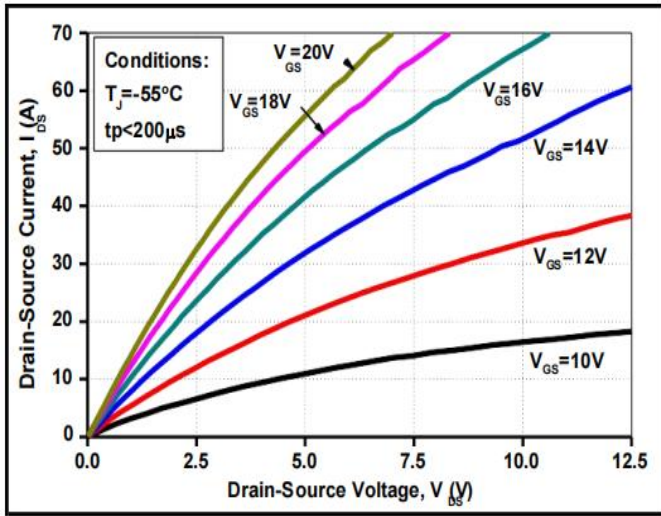


Figure 1. Output Characteristics $T_J = -55^\circ\text{C}$

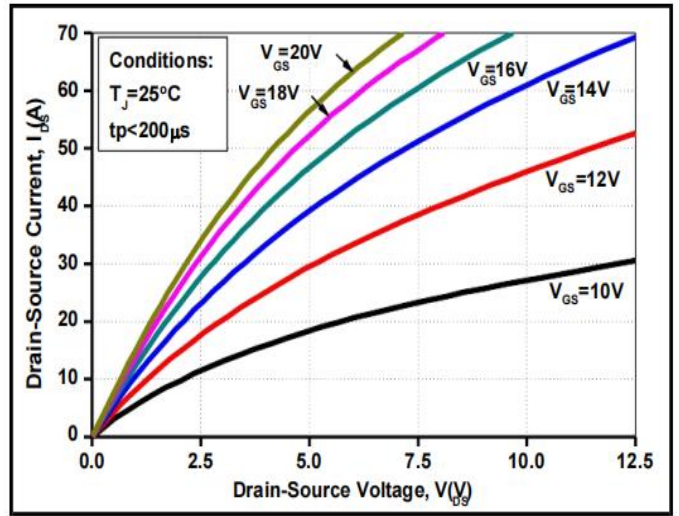


Figure 2. Output Characteristics $T_J = 25^\circ\text{C}$

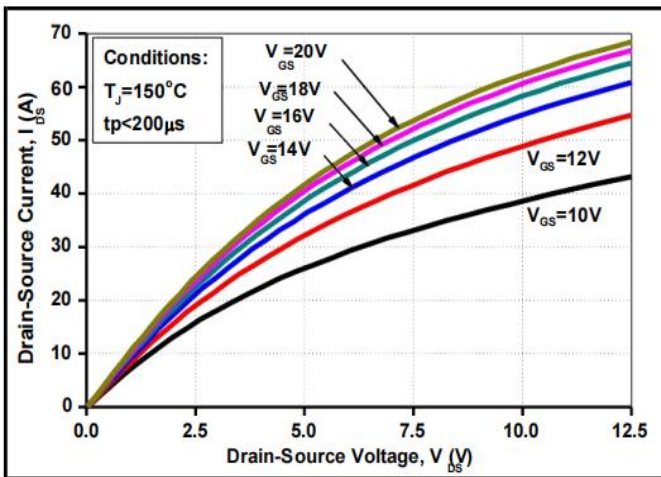


Figure 3. Output Characteristics $T_J = 150^\circ\text{C}$

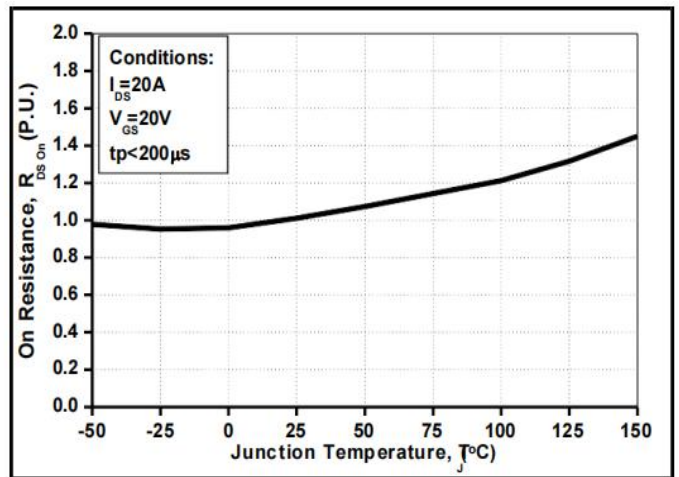


Figure 4. Normalized On-Resistance vs. Temperature

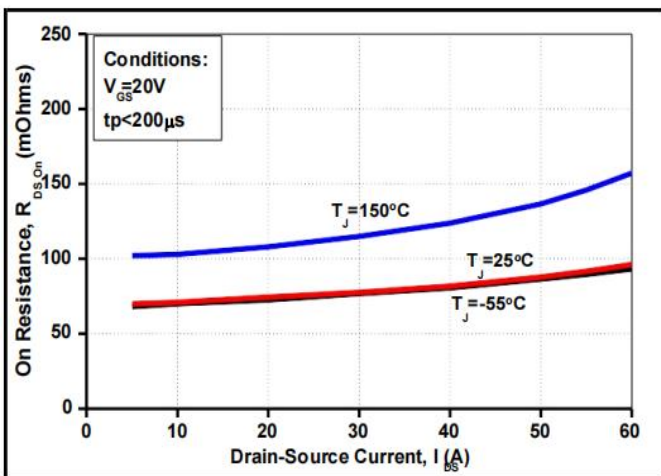


Figure 5. On-Resistance vs. Drain Current

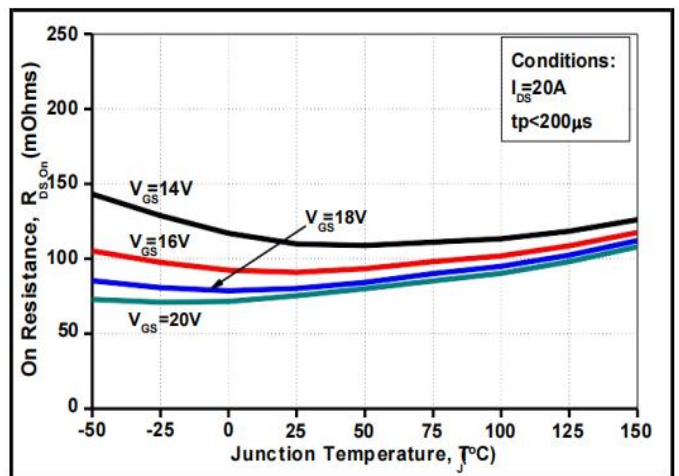


Figure 6. On-Resistance vs. Temperature

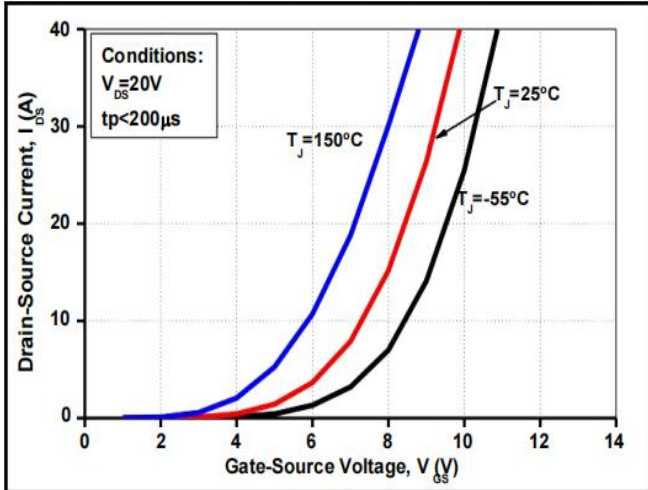


Figure 7. Transfer Characteristic for Various Junction Temperatures

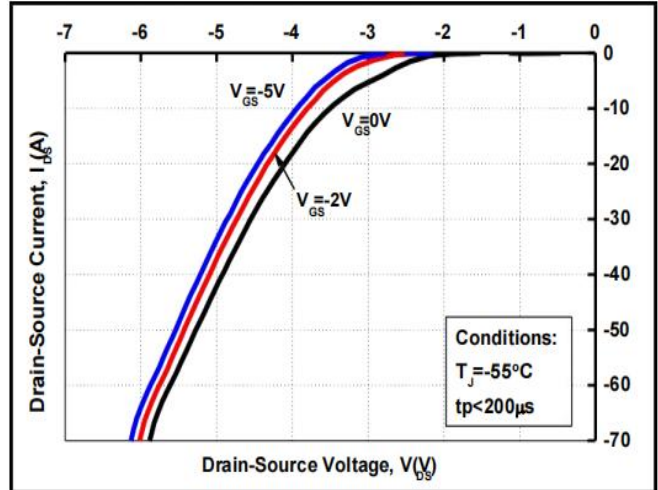


Figure 8. Body Diode Characteristic at -55 °C

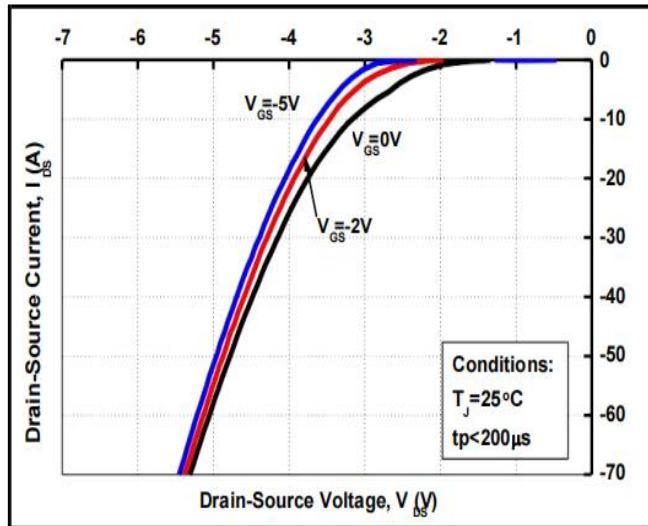


Figure 9. Body Diode Characteristic at 25 °C

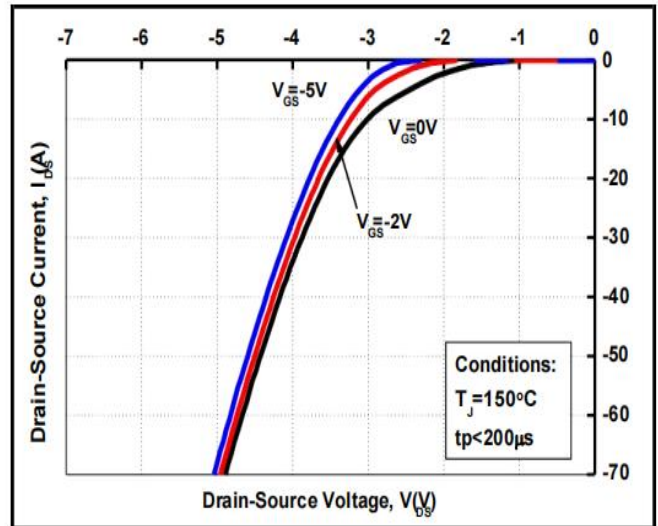


Figure 10. Body Diode Characteristic at 150 °C

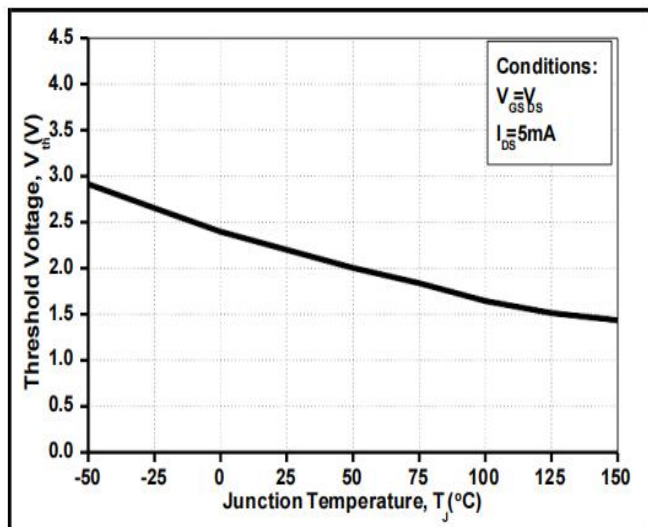


Figure 11. Threshold Voltage vs. Temperature

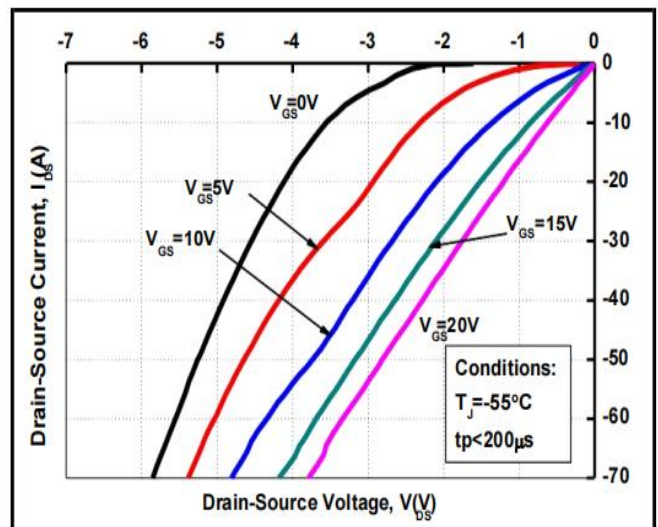


Figure 12. 3rd Quadrant Characteristic at -55 °C

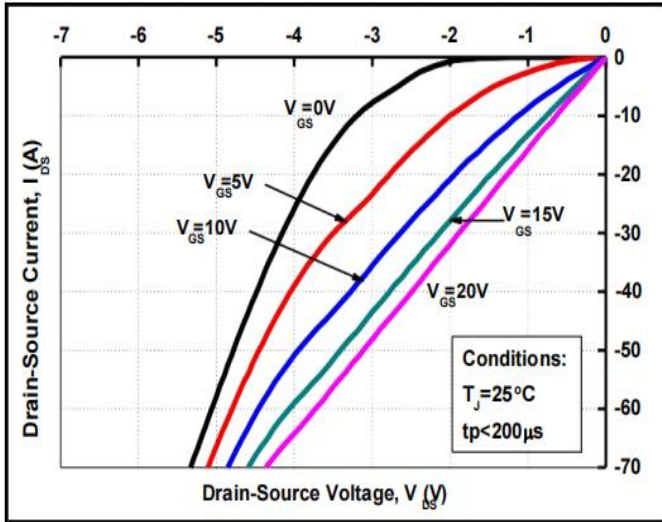


Figure 13. 3rd Quadrant Characteristic at 25 °C

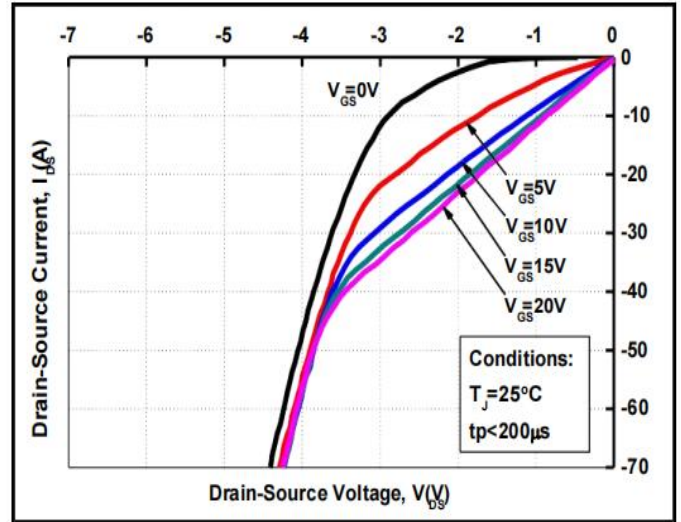


Figure 14. 3rd Quadrant Characteristic at 150 °C

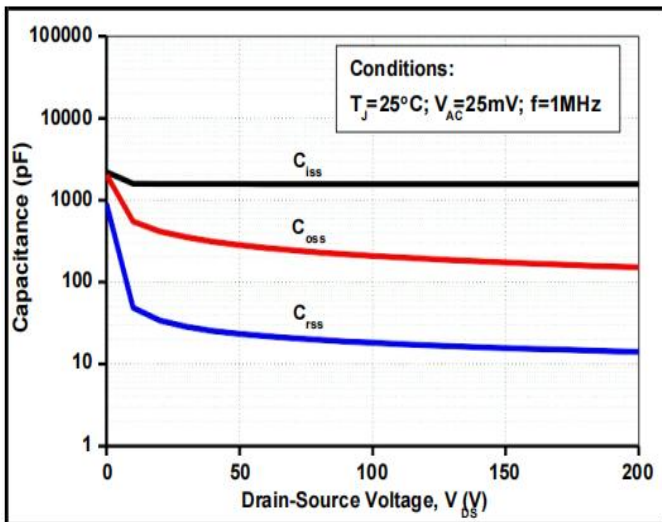


Figure 15. Capacitances vs. Drain-Source Voltage (0 - 200V)

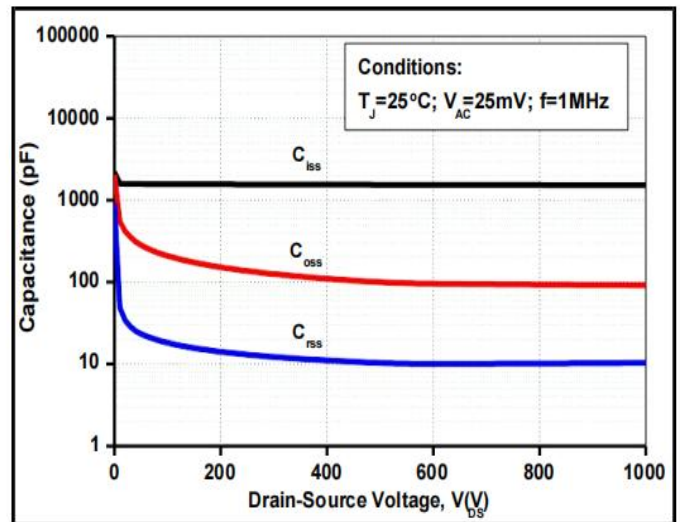
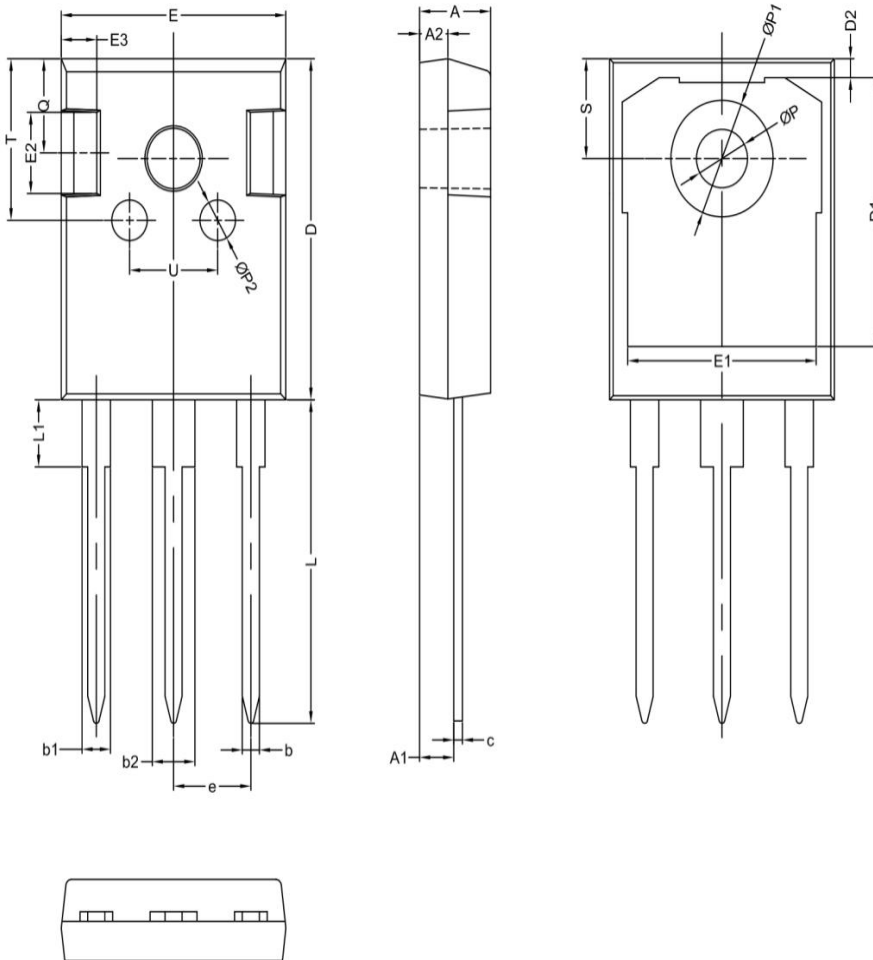


Figure 16. Capacitances vs. Drain-Source Voltage (0 - 1000V)

Package outline drawing(TO-247-3 Unit: mm)



| 符号 | 机械尺寸/mm | | |
|----|---------|-------|-------|
| | 最小值 | 典型值 | 最大值 |
| A | 4.80 | 5.00 | 5.20 |
| A1 | 2.21 | 2.41 | 2.61 |
| A2 | 1.90 | 2.00 | 2.10 |
| b | 1.10 | 1.20 | 1.35 |
| b1 | | 2.00 | |
| b2 | | 3.00 | |
| c | 0.55 | 0.60 | 0.75 |
| D | 20.80 | 21.00 | 21.20 |
| D1 | | 16.55 | |
| D2 | | 1.20 | |
| E | 15.60 | 15.80 | 16.0 |
| E1 | | 13.30 | |
| E2 | | 5.00 | |
| E3 | | 2.50 | |
| e | | 5.44 | |
| L | 19.42 | 19.92 | 20.42 |
| L1 | | 4.13 | |
| P | 3.50 | 3.60 | 3.70 |
| P1 | - | - | 7.40 |
| P2 | | 2.50 | |
| Q | | 5.80 | |
| S | 6.05 | 6.15 | 6.25 |
| T | | 10.00 | |
| U | | 6.20 | |

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